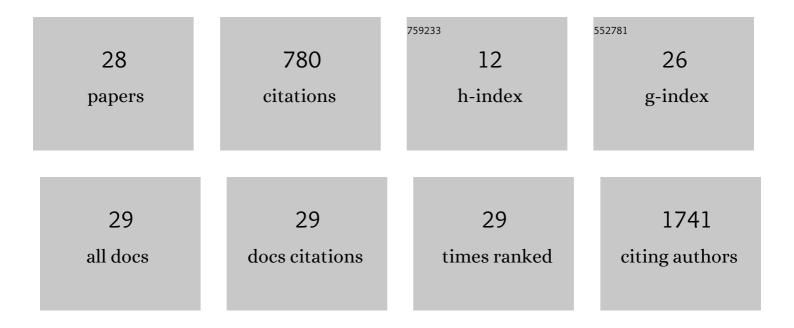
## Jae-Keun Kim

List of Publications by Year in descending order

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INE-KELINI KIM

#	Article	IF	CITATIONS
1	Electrical and Optical Characterization of MoS <sub>2</sub> with Sulfur Vacancy Passivation by Treatment with Alkanethiol Molecules. ACS Nano, 2015, 9, 8044-8053.	14.6	185
2	Enhancement of photodetection characteristics of MoS <sub>2</sub> field effect transistors using surface treatment with copper phthalocyanine. Nanoscale, 2015, 7, 18780-18788.	5.6	101
3	Transparent Large-Area MoS <sub>2</sub> Phototransistors with Inkjet-Printed Components on Flexible Platforms. ACS Nano, 2017, 11, 10273-10280.	14.6	72
4	Enhanced Charge Injection Properties of Organic Field‣ffect Transistor by Molecular Implantation Doping. Advanced Materials, 2019, 31, e1806697.	21.0	60
5	Contactâ€Engineered Electrical Properties of MoS <sub>2</sub> Fieldâ€Effect Transistors via Selectively Deposited Thiolâ€Molecules. Advanced Materials, 2018, 30, e1705540.	21.0	56
6	Trap-mediated electronic transport properties of gate-tunable pentacene/MoS2 p-n heterojunction diodes. Scientific Reports, 2016, 6, 36775.	3.3	54
7	Two-Dimensional Thickness-Dependent Avalanche Breakdown Phenomena in MoS <sub>2</sub> Field-Effect Transistors under High Electric Fields. ACS Nano, 2018, 12, 7109-7116.	14.6	43
8	Intrinsic Optoelectronic Characteristics of MoS <sub>2</sub> Phototransistors <i>via</i> a Fully Transparent van der Waals Heterostructure. ACS Nano, 2019, 13, 9638-9646.	14.6	43
9	Ultrasensitive Photodetection in MoS <sub>2</sub> Avalanche Phototransistors. Advanced Science, 2021, 8, e2102437.	11.2	34
10	Molecular Dopantâ€Dependent Charge Transport in Surfaceâ€Chargeâ€Transferâ€Doped Tungsten Diselenide Field Effect Transistors. Advanced Materials, 2021, 33, e2101598.	21.0	20
11	Analysis of the interface characteristics of CVD-grown monolayer MoS <sub>2</sub> by noise measurements. Nanotechnology, 2017, 28, 145702.	2.6	14
12	Trapped charge modulation at the MoS <sub>2</sub> /SiO <sub>2</sub> interface by a lateral electric field in MoS <sub>2</sub> field-effect transistors. Nano Futures, 2019, 3, 011002.	2.2	13
13	Enhanced Output Performance of All-Solution-Processed Organic Thermoelectrics: Spray Printing and Interface Engineering. ACS Applied Materials & Interfaces, 2020, 12, 26250-26257.	8.0	10
14	Crystallinity-dependent device characteristics of polycrystalline 2D n = 4 Ruddlesden–Popper perovskite photodetectors. Nanotechnology, 2021, 32, 185203.	2.6	10
15	Analysis of noise generation and electric conduction at grain boundaries in CVD-grown MoS <sub>2</sub> field effect transistors. Nanotechnology, 2017, 28, 47LT01.	2.6	9
16	Effect of Facile p-Doping on Electrical and Optoelectronic Characteristics of Ambipolar WSe2 Field-Effect Transistors. Nanoscale Research Letters, 2019, 14, 313.	5.7	9
17	Channel-Length-Modulated Avalanche Multiplication in Ambipolar WSe <sub>2</sub> Field-Effect Transistors. ACS Nano, 2022, 16, 5376-5383.	14.6	9
18	Resistive Switching by Percolative Conducting Filaments in Organometal Perovskite Unipolar Memory Devices Analyzed Using Current Noise Spectra. Advanced Functional Materials, 2022, 32, 2107727.	14.9	8

JAE-KEUN KIM

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19	Effects of Electron Beam Irradiation and Thiol Molecule Treatment on the Properties of MoS2 Field Effect Transistors. Journal of the Korean Physical Society, 2018, 72, 1203-1208.	0.7	7
20	Highly uniform monolayer graphene synthesis <i>via</i> a facile pretreatment of copper catalyst substrates using an ammonium persulfate solution. RSC Advances, 2019, 9, 20871-20878.	3.6	6
21	Dose-dependent effect of proton irradiation on electrical properties of WSe <sub>2</sub> ambipolar field effect transistors. Nanoscale, 2019, 11, 13961-13967.	5.6	5
22	Tailored Designâ€ofâ€Experiments Approach for Device Performance Prediction and Optimization of Flashâ€Evaporated Organic–Inorganic Halide Perovskiteâ€Based Photodetectors. Advanced Materials Technologies, 2021, 6, 2001131.	5.8	5
23	Enhanced Photoâ€Response of Mos 2 Photodetectors by a Laterally Aligned SiO 2 Nanoribbon Array Substrate. ChemNanoMat, 2019, 5, 1272-1279.	2.8	2
24	Organic Field-Effect Transistors: Enhanced Charge Injection Properties of Organic Field-Effect Transistor by Molecular Implantation Doping (Adv. Mater. 10/2019). Advanced Materials, 2019, 31, 1970073.	21.0	2
25	Role of Two-Dimensional Ising Superconductivity in the Nonequilibrium Quasiparticle Spin-to-Charge Conversion Efficiency. ACS Nano, 2021, 15, 16819-16827.	14.6	2
26	Fieldâ€Effect Transistors: Contactâ€Engineered Electrical Properties of MoS <sub>2</sub> Fieldâ€Effect Transistors via Selectively Deposited Thiolâ€Molecules (Adv. Mater. 18/2018). Advanced Materials, 2018, 30, 1870129.	21.0	1
27	Perovskite Photodetector Devices: Tailored Designâ€ofâ€Experiments Approach for Device Performance Prediction and Optimization of Flashâ€Evaporated Organic–Inorganic Halide Perovskiteâ€Based Photodetectors (Adv. Mater. Technol. 5/2021). Advanced Materials Technologies, 2021, 6, 2170029.	5.8	0
28	Introduction to Molecular Interface Engineering of Transition Metal Dichalcogenide-based Devices. , 2021, , 43-91.		0